Basic Electrical and Electronics Engineering-I
Code: ES101
Contacts: 3L + 1T = 4
Credits: 4

Basic Electrical Engineering-I

DC Network Theorem: Definition of electric circuit, network, linear circuit, non-linear circuit, bilateral circuit, unilateral circuit, Dependent source, Kirchhoff's law, Principle of superposition. Source equivalence and conversion, Thevenin's theorem, Norton Theorem, nodal analysis, mesh analysis, star-delta conversion. Maximum power transfer theorem with proof. 7L

Electromagnetism: Biot-savart law, Ampere's circuital law, field calculation using Biot-savart & ampere's circuital law. Magnetic circuits, Analogous quantities in magnetic and electric circuits, Faraday's law, Self and mutual inductance. Energy stored in a magnetic field, B-H curve, Hysteretic and Eddy current losses, Lifting power of Electromagnet. 5L

AC fundamental: Production of alternating voltage, waveforms, average and RMS values, peak factor, form factor, phase and phase difference, phasor representation of alternating quantities, phasor diagram, behavior of AC series , parallel and series parallel circuits, Power factor, Power in AC circuit, Effect of frequency variation in RLC series and parallel circuits, Resonance in RLC series and parallel circuit, Q factor, band width of resonant circuit. 9L

Basic Electronics Engineering-I

Recapitulation and Orientation lectures: 2L
Module – 1: Semiconductors: 4L
Crystalline material: Mechanical properties, Energy band theory, Fermi levels; Conductors, Semiconductors and Insulators: electrical properties, band diagrams. Semiconductors: intrinsic and extrinsic, energy band diagram, electrical conduction phenomenon, P-type and N-type semiconductors, drift and diffusion carriers.

Module – 2: Diodes and Diode Circuits: 3L+3L = 6L
Formation of P-N junction, energy band diagram, built-in-potential forward and reverse biased P-N junction, formation of depletion zone, V-I characteristics, Zener breakdown, Avalanche breakdown and its reverse characteristics; Junction capacitance and Varactor diode.

Simple diode circuits, load line, linear piecewise model; Rectifier circuits: half wave, full wave, PIV, DC voltage and current, ripple factor, efficiency, idea of regulation.

Module – 3: Bipolar Junction Transistors: 6L+2L = 8L
Formation of PNP / NPN junctions, energy band diagram; transistor mechanism and principle of transistors, CE, CB, CC configuration, transistor characteristics: cut-off active and saturation mode, transistor action, injection efficiency, base transport factor and current amplification factors for CB and CE modes.

Biasing and Bias stability: calculation of stability factor;

Recommended Books:
Text:
1. Sedra & Smith: Microelectronics Engineering.
2. Millman & Halkias: Integrated Electronics.
References:
1. Boylestad & Nashelsky: Electronic Devices & Circuit Theory
2. Salivahanan: Electronics Devices & Circuits.

Basic Electrical and Electronics Engineering-I
Code: ES191
Contacts:
Credits: 2
Basic Electrical Engineering Laboratory-I
List of Experiments:
1. Characteristics of Fluorescent lamps
2. Characteristics of Tungsten and Carbon filament lamps
3. (a) Verification of Thevenin's theorem.
   (b) Verification of Norton's theorems.
4. Verification of Maximum power theorem.
5. Verification of Superposition theorem
6. Study of R-L-C Series circuit
7. Study of R-L-C parallel circuit

Basic Electronics Engineering Laboratory-I
• There will be a couple of familiarization lectures before the practical classes are undertaken where basic concept of the instruments handled Eg: CRO, Multimeters etc will be given. Lectures on measurement techniques and error calculation will also have to be organized.
• 3 hours per week must be kept, initially for practical lectures, and later for tutorials.

List of Experiments:
1. Familiarisation with passive and active electronic components such as Resistors, Inductors, Capacitors, Diodes, Transistors (BJT) and electronic equipment like DC power supplies, multimeters etc.
2. Familiarisation with measuring and testing equipment like CRO, Signal generators etc.
3. Study of I-V characteristics of Junction diodes.
4. Study of I-V characteristics of Zener diodes.
5. Study of Half and Full wave rectifiers with Regulation and Ripple factors.
6. Study of I-V characteristics of BJTs.